

PATENT

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- 5 forming a gate on the gate oxide;  
6 implanting a first pocket implant into the semiconductor substrate from a  
7 first side of the gate; and  
8 implanting a second pocket implant into the semiconductor substrate from  
9 a second side of the gate, wherein the first pocket implant is near and separated by a  
10 small distance from the second pocket implant.

38. (Amended) A method of fabricating a transistor in an integrated  
circuit device comprising:  
providing a semiconductor substrate having a surface;  
forming a gate oxide on the semiconductor substrate surface;  
forming a gate on the gate oxide;  
implanting a first pocket implant into the semiconductor substrate from a  
first side of the gate at an angle; and  
implanting a second pocket implant into the semiconductor substrate from  
a second side of the gate at an angle,  
wherein a concentration of the pocket implants under the gate is  
nonuniform, and the pocket implants extend near the semiconductor substrate surface.

41. (New) The method of claim 27 wherein the first pocket  
implant is separated from the second pocket implant by approximately 0.35 microns.